

	Sunday 19/5	Monday 20/5	Tuesday 21/5	Wednesday 22/5	Thursday 23/5
8:40		<b>Conference Opening</b>			
8:50			<b>Huili Grace Xing</b>	<b>Béla Pécz</b>	<b>Daniel Lichtenwalner</b>
9:00			HEMT based on GaN/AlN heterostructures	Advanced TEM characterization of compound semiconductors and 2D materials	Key Electrical Aspects of N and Al doped 4H-SiC: Measurements and Modelling
9:10					
9:20					
9:30		<b>Volker Ziegler</b>	<b>Y. Cordier</b>	<b>P. Komninou</b>	<b>E. Vandermolen</b>
9:40		For the skies: Exploring tomorrow's microwave technologies	ScAlN/GaN HEMTs grown by ammonia source molecular beam epitaxy	Unlocking the Limits of Monolayer-thick InGaN/GaN Quantum Wells: A Combined Experimental and Theoretical Analysis	DLTS Investigation of Implantation-induced Defects in 4H-SiC Power Diodes
9:50		<b>Th. Kaltsounis</b>	<b>D. Pavlidis</b>	<b>P. Vennéguès</b>	<b>F. La Via</b>
10:00		700 V BV quasi-vertical p-n diode by localized epitaxial growth of GaN on Si wafer	Field Emission Properties of Top-Down GaN Nanowire Arrays Using Nanoresolution and Variable Vacuum Characterization Techniques	In-depth investigation of the GaN nanowires Si-assisted MOVPE growth mechanism	Heavy ions radiation damage on silicon and silicon carbide detectors
10:10		<b>M. El Amrani</b>	<b>E. Iliopoulos</b>	<b>G. Dimitrakopoulos</b>	<b>A. S. Mancuso</b>
10:20		Reverse Leakage Mechanism of GaN Pseudo-Vertical p-n Diode Grown on Si by Localized Epitaxy	Magnetotransport Investigations of Low Density AlGaIn/GaN 2DEGs	Strain behavior of GaAs/In(Ga)As core-shell nanowires	Temperature Dependence of Current-Voltage characteristics of High-Voltage SiC PN diode
10:30-10:50		<b>A. Barbier-Cueil</b>	<b>Y.-H. Chen</b>	<b>M. Leszczynski</b>	<b>M. Gavalas</b>
10:50		Buffer engineering of AlGaIn channel transistors on silicon grown by Molecular Beam Epitaxy for high voltage applications	Threshold voltage variations in Schottky-Gate HEMT MIS-HEMT down to Cryogenic Temperatures	X-ray Diffraction Method to Distinguish Between Indium and Thickness Fluctuations in InGaN Multiple Quantum Wells	Growth of n-doped polycrystalline SiC thin films by chemical vapor deposition for brain-implantable devices
11:00		<b>Q. Shu</b>	<b>F. Grandpierron</b>	<b>L. Nieto Sierra</b>	<b>S. Greenhorn</b>
11:10		Investigation of Etch-Damage Minimization for Vertical GaN Devices	Impact of Carbon-doped AlGaIn back barrier in AlN/GaN/AlGaIn HEMTs	Comparative TEM study of Si(111) and diamond coated Si(111) as substrates for the sputtering deposition of piezoelectric AlN thin films	Composition and structure determination of PECVD amorphous silicon carbide: techniques, synergies, and optimization
11:20			<b>L. Ben Hammou</b>	<b>G. Trovato</b>	<b>C.-G. Nunez</b>
11:30			Investigation of the origin of deep levels in Carbon-doped AlN/GaN/AlGaIn HEMTs	SiC free-standing membrane characterization with X-Ray beams	Study of ZnO triboelectric material as top-gate electrode in mechanically actuated CMOS-based tribotronic devices
11:40		<b>Coffee break</b>	<b>Coffee break</b>	<b>Coffee break</b>	<b>Coffee break</b>
11:50			<i>Jeol presentation</i>	<i>Zeiss presentation</i>	
12:00		<b>Tetsu Kachi</b>	<b>Enrico Bellotti</b>	<b>Jakub Cizek</b>	<b>Kostantinos Rogdakis</b>
12:10		Selective p-type doping for vertical GaN power devices	Theoretical Models of Ultra-Wide Band Gap Semiconductor Materials and Devices	Study of vacancies in GaN crystals and thin films by positron annihilation spectroscopy	Perovskites meet 2D materials: A novel materials platform for efficient energy harvesting and neuromorphics
12:20		<b>S. Kumar</b>	<b>L. Lymparakis</b>	<b>F. Hájek</b>	<b>J. Novak</b>
12:30		1200 V lateral p-GaN HEMTs on engineered polycrystalline AlN substrates	A comparative study of screw and mixed type dislocations in GaN	Correlation of Raman and luminescence spectroscopy with positron annihilation spectroscopy on ammonothermal GaN	Creation of thin Ga2Se3 PN junction during the PSe2 preparation
12:40		<b>A. Karimi</b>	<b>S. Lepkowski</b>	<b>S. Besendörfer</b>	<b>S.-N. Pikou</b>
12:50-14:30		Plasma-assisted atomic layer-etching process for GaN NW-based power electronics	Topological Insulator in Ultra-Thin InN/nGaIn Coupled Quantum Wells	Inspection of dislocation content and strain of PVT-grown AlN bulk crystals utilizing a combined X-Ray Topography and Raman scattering approach	Exciton recombination dynamics in MAPbCl3 single crystals
13:00		<b>J. Marek</b>	<b>C. Katsidis</b>	<b>J. Arvanitidis</b>	<b>C. Sliatanidou</b>
13:10		The impact of electric stress on charge trap states in SiC-based TrenchMOS	Depth Profiling of Electrons Confined in Indium Nitride Nano-Heterostructures	Comparative high pressure Raman and photoluminescence study of bulk and 'substrate-free' two-dimensional MoS2	Dual-wavelength lasing in a MAPbCl3 vertical-cavity surface-emitting laser
13:20		<b>S. Chakraborty</b>	<b>M. Bucher</b>	<b>A. Hospodková</b>	<b>N. Chatzarakis</b>
13:30		Charging Profile-Oriented Design for Reliability (DPR) Analysis of a WBG-based Multi-Use DC Charger Using a System-Level Electrothermal Model	GaN HEMT Parameter Extraction from AC Capacitances	Influence of buffer surface morphology on PL properties of InGaIn/GaN MQW	MAPbI3 on GaAs: a heterointerface with giant passivation effect
13:40		<b>M. Minarik</b>	<b>A. Chvala</b>	<b>M. Hugues</b>	<b>Victor Veliadis</b>
13:50		Fast short circuit protection for SiC power modules	Simulation Analysis of Nanomembrane GaAs HEMT on Foreign Substrates	GaN detector array for high-energy proton beam imaging	Accelerating WBG Power Semiconductor Technology Commercialization
14:00		<b>S. Kumar Bhol</b>	<b>P. Beleniotis</b>	<b>M. Matuš</b>	
14:10		Mission Profile-Oriented Reliability Assessment of a GaN-based On-Board Charger	A Computational Modeling Method for Performance Optimization of GaN HEMT	Study of InGaIn/GaN Quantum Well structure using transient spectroscopy	
14:20					
14:30		<b>Lunch in MARINA</b>	<b>Lunch in PSARADES</b>	<b>Lunch in TENNIS CLUB</b>	<b>Student Awards Ceremony &amp; Closing Remarks</b>
14:40					
14:50					
15:00		<b>Jeongsun Moon</b>	<b>Dimosthenis Pefitsis</b>		<b>Lunch in MARE</b>
15:10		Millimeter-wave GaN opportunities and challenges	SiC MOSFETs enabling high performance inverted designs		
15:20		<b>V. Ackermann</b>	<b>R. Menozzi</b>		
15:30		Alumina gate dielectric integration for fully-vertical GaN MOSFETs	In-circuit Characterization Procedure of Three Temperature-Sensitive Electric Parameters for SiC MOSFETs		
15:40		<b>J.I Asubar</b>	<b>J. Nuzzo</b>		
15:50		Interface characterization of regrown-AlGaIn/ZrO2 Interfaces for Normally-off GaN-based MIS-HEMTs	Application-Oriented Active Power Cycling of SiC MOSFET Power Modules with Multiple TSEP Acquisition		
16:00		<b>E. Schillrö</b>	<b>F. La Via</b>		
16:10-16:30		Effects of annealing treatment on vertical AlZrO3/GaN capacitors	Stress fields distribution and simulation in 3C-SiC resonators		
16:30		<b>Q. Paoli</b>	<b>B.-O. Vale Tabernero</b>		
16:40		Robustness of the Au/Ni ohmic contact on p-type GaN through microelectronic manufacturing processes	GaN Schottky Metallization based on Pt and Ni Anode on sapphire substrate with ultra-low reverse leakage current		
16:50		<b>H. Yazdani</b>	<b>M. Mamor</b>		
17:00		Optimum Lateral Distance Between Recess and Metallization in Recessed Ohmic Contact Technology for RF HEMTs	Investigation of barrier height inhomogeneities in metal/n-type GaN Schottky contacts		
17:10		<b>M. Chae</b>	<b>G. Greco</b>		
17:20		Observation of Threshold Voltage Instability by Varying Stress Bias and Temperature in E-mode AlGaIn/GaN HEMTs	Forward conduction mechanism in W-based Schottky contacts on AlGaIn/GaN heterostructures		
17:30		<b>K. Gaffar</b>	<b>A. Al Abdallah</b>		
17:40		Multi-technique Characterization of GaN-based HEMT: towards a better understanding of the electrical response	Thermal Annealing Effects on The Electrical Properties of Mo/Au and Pt/Au Schottky Contacts on n-GaN		
17:50					
18:00		<b>Coffee break</b>	<b>Coffee break</b>	<b>Excursion in Spinaloga &amp; Dinner in Plaka</b>	
18:10-18:30					
18:30		<b>Bianchi Mendez</b>	<b>N. Ravier: JEOL presentation</b>		
18:40		New trends on wide bandgap oxides for photonic applications	Latest JEOL applications in electron beam lithography: How high tension up to 200kV influences your results		
18:50		<b>M. Gajdics</b>	<b>O. Vertsanova: Zeiss presentation</b>		
19:00-19:00		Reactive Sputter Deposition of Ga2O3 and GaON Thin Films Using Liquid Ga Target	Zeiss advanced solutions for high resolution imaging, sample preparation and correlative microscopy workflow for semiconductor materials characterization		
19:00-19:00		<b>J.-C. Mendes</b>	<b>A. Garnache</b>		
19:10		Functionalization of Diamond Surfaces Using an UV Laser Source	Structured Opto-Thz coherent light sources based on III-V semiconductor laser technology		
19:20		<b>D.K. Sharma</b>	<b>V. Apostolopoulos</b>		
19:30		Gas composition-controlled growth of boron doped diamond films by microwave plasma CVD process	Adaptive membrane quantum well waveguide lasers		
19:40		<b>P. Dimitrakis</b>	<b>N. Chatzarakis</b>		
19:50		Impact of Geometrical Factors of a Single-Layer Graphene device with Interdigitated Electrodes	Enhanced radiative rates in GaAs-based nanowires next to a gold surface due to plasmonic effect		
20:00		<b>J. Keshthkar</b>	<b>A.-G. Carro</b>		
20:10		Fabrication of p-n heterojunction UV-photodetectors based on n-type gallium oxide and p-type boron-doped diamond	Asymmetric Periods For The Complete Optimization of GaAsN/GaAsSb Superlattices Toward Its Implementation In Multi-Junction Solar Cells		
20:20		<b>D. Carrasco</b>	<b>M. Tornay</b>		
20:30		Luminescent and Interferometric Thermometry Using Cr-Doped Ga2O3 Nanowires-based cavities	Structural characterization of InAs/InAsSb type-II superlattice to determine real band edge potential profile		
20:40		<b>B.-R. Fernandez</b>	<b>H. Jeddi</b>		
20:50		Polyvinyl Alcohol/Graphene Quantum Dots Nanocomposites: structural and luminescent properties	Infrared Photodetectors based on InP/InAsP Quantum Discs-in-Nanowire Heterostructures		
21:00-21:00		<b>Registration Welcome Reception in Tennis Club</b>			